Symposium (Oral) | Symposium | Materials Science and Advanced Electronics Created by Singularity of Nitride Semiconductors ~Crystal Growth, Characterization and Application for Advanced GaN Electron Devices~

[6p-A301-1~7]Materials Science and Advanced Electronics Created by Singularity of Nitride Semiconductors ~Crystal Growth, Characterization and Application for Advanced GaN Electron Devices~

Tamotsu Hashizume(Hokkaido Univ.)

Wed. Sep 6, 2017 1:00 PM - 4:30 PM A301 (Main Hall)

△:奨励賞エントリー

▲:英語発表

▼:奨励賞エントリーかつ英語発表

空欄:どちらもなし

1:00 PM - 1:10 PM

## [6p-A301-1]Introductory Talk

OHiroshi Fujioka<sup>1</sup> (1.The Univ. of Tokyo)

Keywords:nitride semiconductors